



STP8NS25 STP8NS25FP

N-CHANNEL 250V - 0.38Ω - 8A TO-220/TO-220FP
MESH OVERLAY™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP8NS25	250 V	< 0.45 Ω	8 A
STP8NS25FP	250 V	< 0.45 Ω	8 A

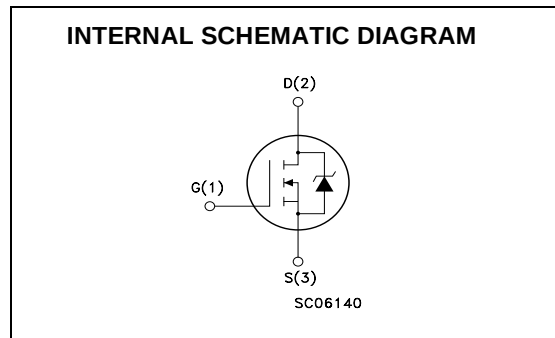
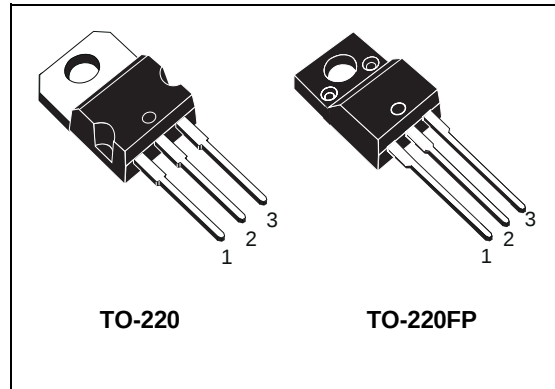
- TYPICAL R_{DS(on)} = 0.38 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performance. The new patented STrip layout coupled with the Company's proprietary edge termination structure, makes it suitable in converters for lighting applications.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-DC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP8NS25	STP8NS25FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	250		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	250		V
V _{GS}	Gate- source Voltage	± 20		V
I _D	Drain Current (continuous) at T _C = 25°C	8	8(*)	A
I _D	Drain Current (continuous) at T _C = 100°C	5	5(*)	A
I _{DM} (•)	Drain Current (pulsed)	32	32(*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	80	30	W
	Derating Factor	0.64	0.24	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	-	2000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _J	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 8A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ T_{JMAX}
(*) Limited only by maximum temperature allowed

STP8NS25/STP8NS25FP

THERMAL DATA

		TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	1.56	4.11	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
R _{thc-sink}	Thermal Resistance Case-sink Typ	0.5		°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300		°C

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	250			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 4 A		0.38	0.45	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} , V _{GS} = 10V		8		A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 4A	7	8		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		770		pF
C _{oss}	Output Capacitance			118		pF
C _{rss}	Reverse Transfer Capacitance			48		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 125\text{ V}$, $I_D = 4\text{ A}$		13		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		18		ns
Q_g	Total Gate Charge	$V_{DD} = 200\text{ V}$, $I_D = 8\text{ A}$, $V_{GS} = 10\text{ V}$		37	51.8	nC
Q_{gs}	Gate-Source Charge			5.2		nC
Q_{gd}	Gate-Drain Charge			14.8		nC

SWITCHING OFF

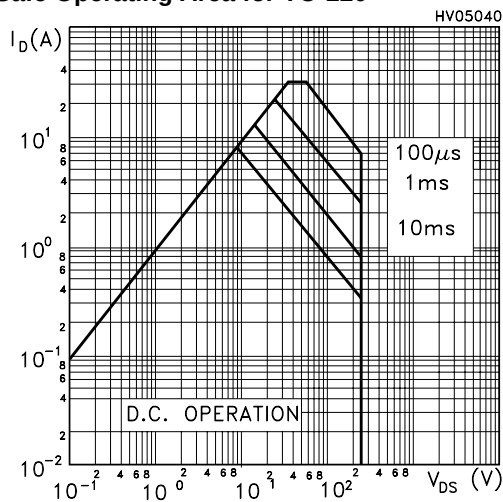
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(voff)}$	Turn-off- Delay Time	$V_{DD} = 125\text{ V}$, $I_D = 4\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		51		ns
t_f	Fall Time			16		ns
$t_{r(voff)}$	Off-voltage Rise Time	$V_{clamp} = 200\text{ V}$, $I_D = 8\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$		12.5		ns
t_f	Fall Time			12.5		ns
t_c	Cross-over Time	(see test circuit, Figure 5)		28		ns

SOURCE DRAIN DIODE

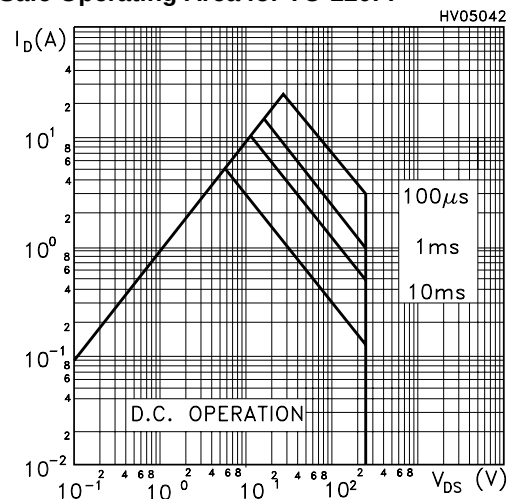
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				32	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 8\text{ A}$, $V_{GS} = 0$			1.7	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$, $T_j = 150^\circ\text{C}$		198		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, Figure 5)		1.1		μC
I_{RRM}	Reverse Recovery Current			11.3		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

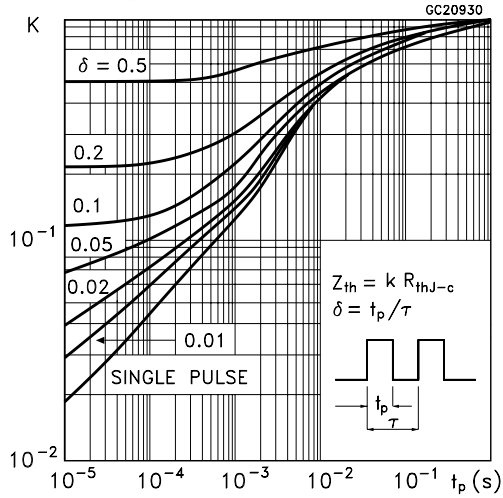
Safe Operating Area for TO-220



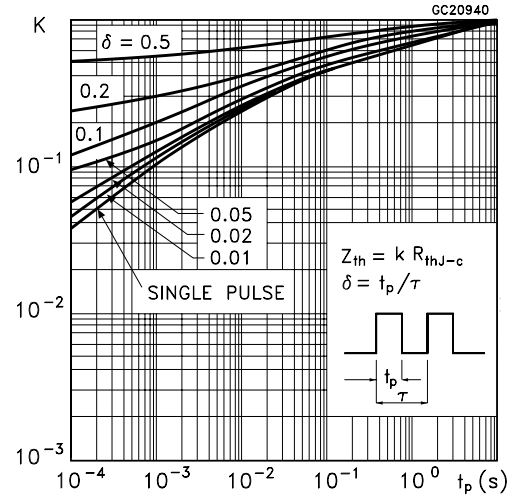
Safe Operating Area for TO-220FP



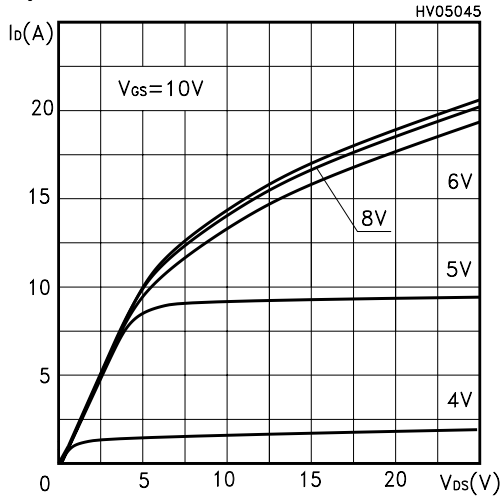
Thermal Impedence for TO-220



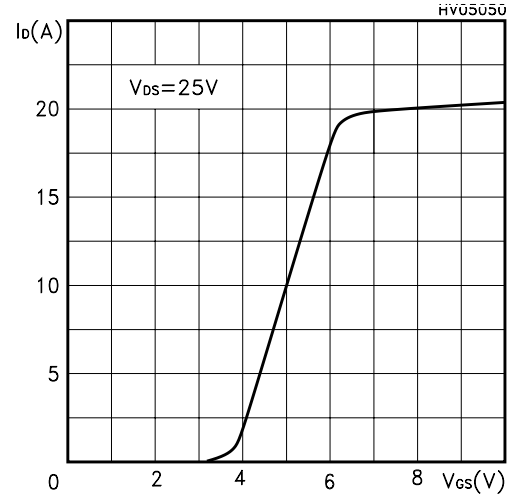
Thermal Impedence for TO-220FP



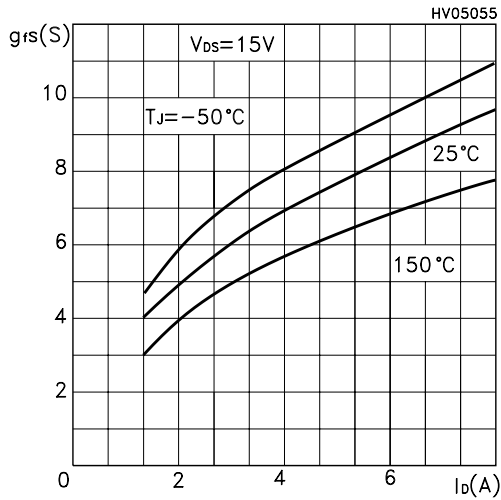
Output Characteristics



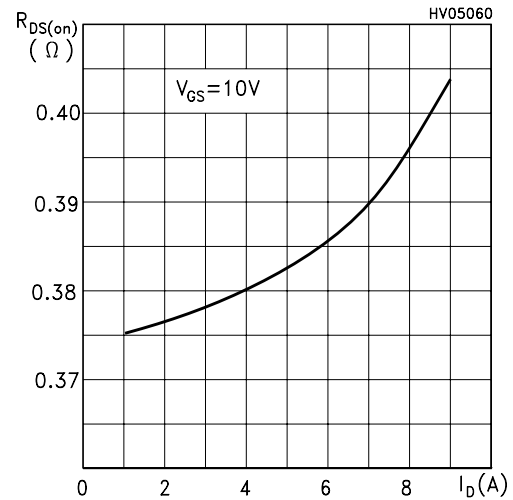
Transfer Characteristics



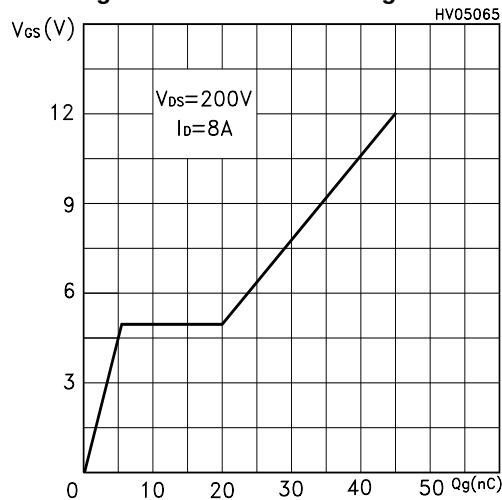
Transconductance



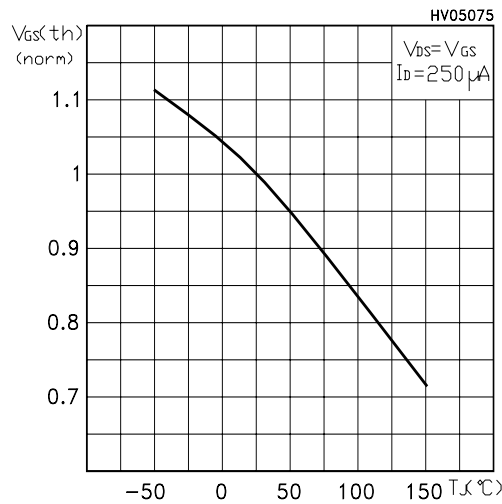
Static Drain-source On Resistance



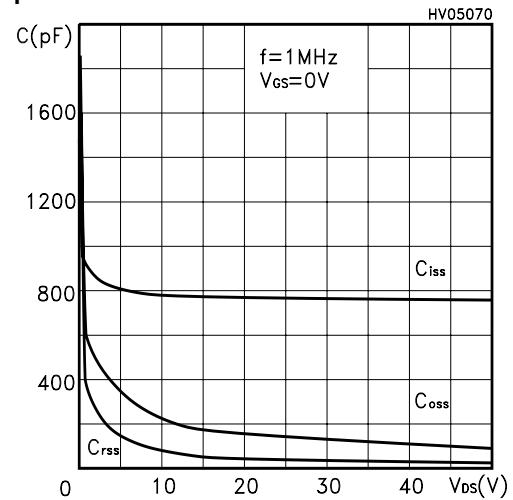
Gate Charge vs Gate-source Voltage



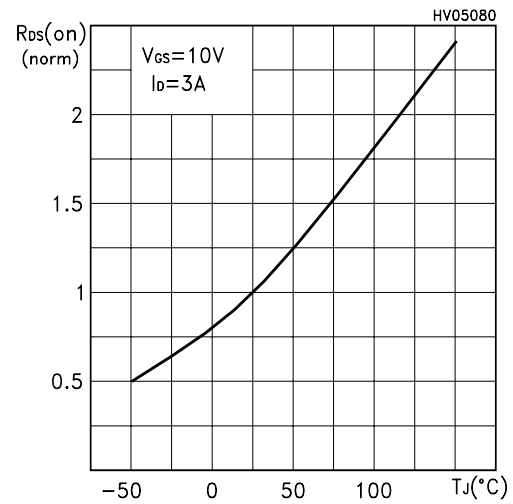
Normalized Gate Threshold Voltage vs Temp.



Capacitance Variations



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

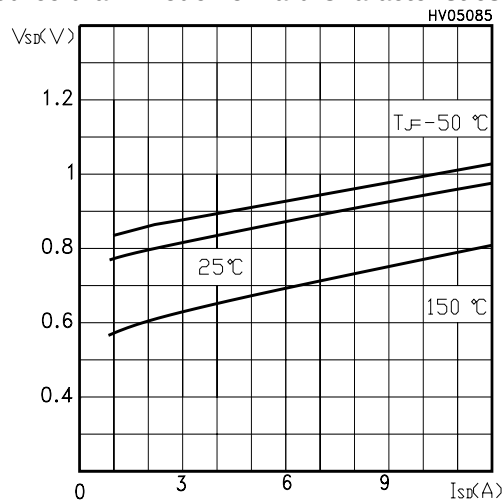


Fig. 1: Unclamped Inductive Load Test Circuit

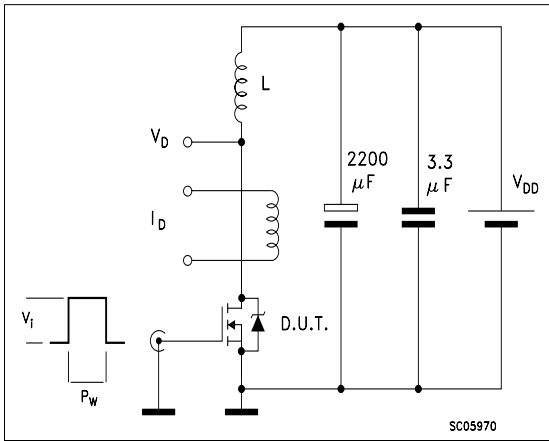


Fig. 2: Unclamped Inductive Waveform

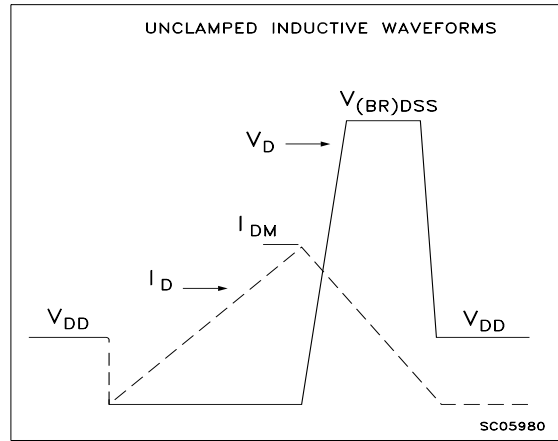


Fig. 3: Switching Times Test Circuit For Resistive Load

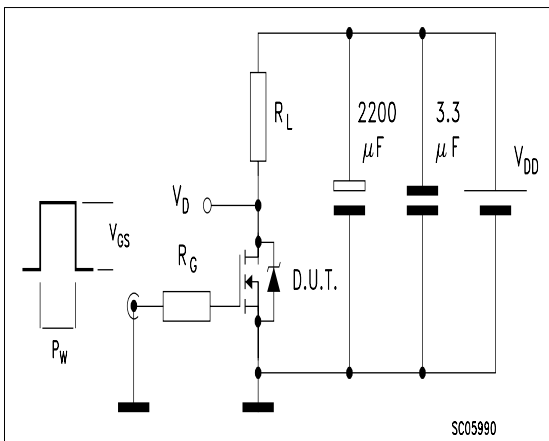


Fig. 4: Gate Charge test Circuit

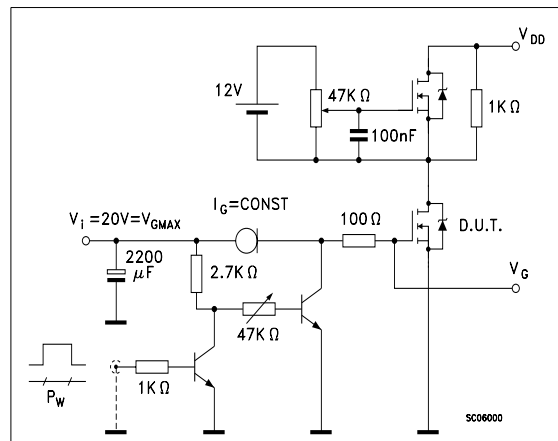
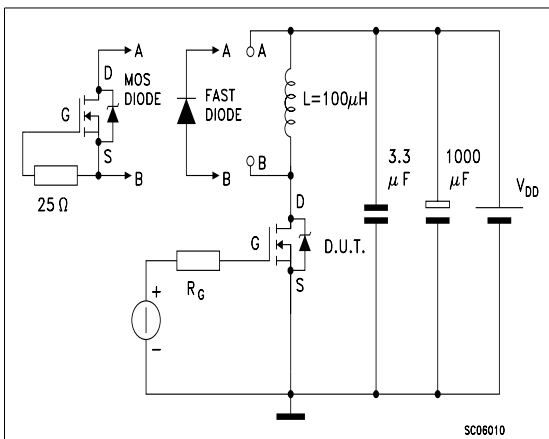


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

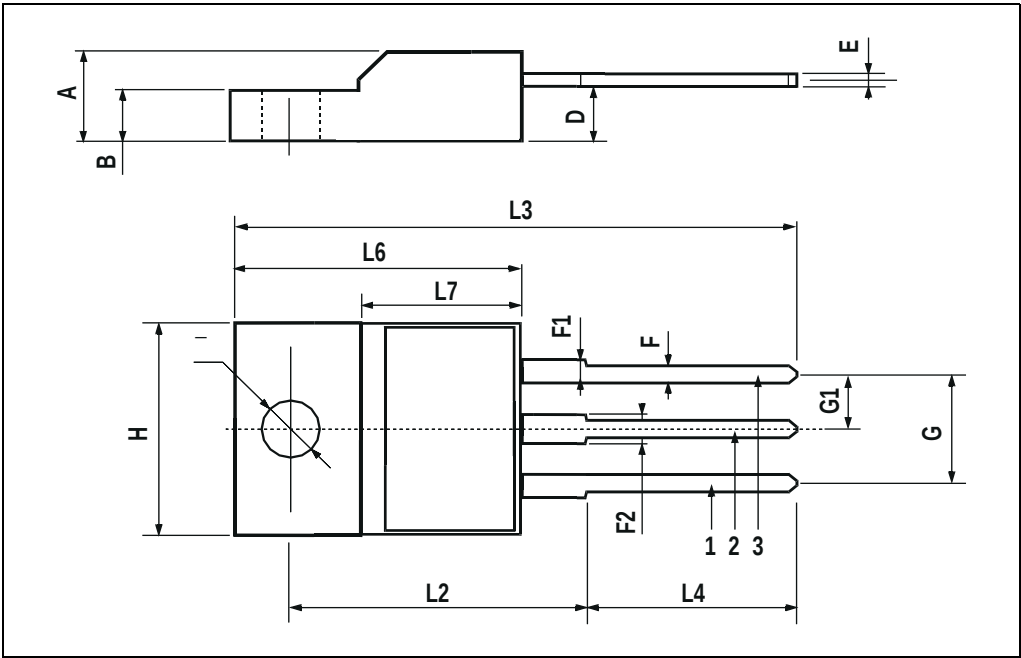


TO-220 MECHANICAL DATA						
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151

P011C

TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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